

7MBR25VA120-50

IGBT Modules

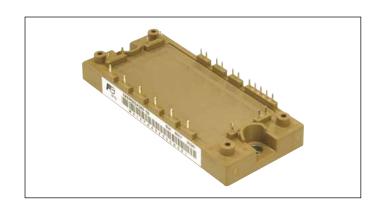
IGBT MODULE (V series) 1200V / 25A / PIM

■ Features

Low V_{CE}(sat)
Compact Package
P.C.Board Mount Module
Converter Diode Bridge Dynamic Brake Circuit
RoHS compliant product

■ Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Collector-Emitter voltage		Vces			1200	V	
Gate-Emitter v	oltage	V _{GES}				V	
5	Collector current	Ic	Continuous	Tc=100°C	25		
Collector curre		Icp	1ms	Tc=80°C	50	٨	
Collector curre		-Ic				Α	
		-I _{c pulse}	1ms	1ms			
Collector power	er dissipation	Pc	1 device	1 device		W	
Collector-Emit	ter voltage	Vces			1200	V	
Gate-Emitter v	oltage	V _{GES}			±20	V	
Collector curre	Collector current	Ic	Continuous	Tc=80°C	25	Α	
S Collector curre		Іср	1ms	Tc=80°C	50	A	
Collector power	er dissipation	Pc	1 device		170	W	
Repetitive pea	Repetitive peak reverse voltage (Diode)					V	
Repetitive pea	epetitive peak reverse voltage					V	
Average outpu	Average output current		50Hz/60Hz, sii	50Hz/60Hz, sine wave		Α	
Average output Surge current	(Non-Repetitive)	I _{FSM}	10ms, T _j =150°C		155	Α	
I²t (Non-Repeti	tive)				120	A ² s	
Junction temperature		_	Inverter, Brake		175		
		Converter		150	°C		
Operating junciton temperature (under switching conditions)		T _{jop} Inverter, Brake Converter		150			
				150			
Case temperature		Tc			125		
Storage temperature		T _{stg}					
solation voltage	between terminal and copper base (*1) between thermistor and others (*2)	Viso	AC : 1min.		2500	VAC	
crew torque	Mounting (*3)	-	M5		3.5	N m	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable value : 2.5-3.5 Nm (M5)

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● Electrical characteristics (at T_i= 25°C unless otherwise specified)

tems		Symbols	Conditions		Characteristics			Units
		Symbols	Conditions	min.	typ.	max.	Units	
Zero gate voltage collector current		Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	1.0	mA
Gate-Emitter leakage current		Iges	V _{GE} = 0V, V _{GE} = ±20V		-	-	200	nA
Gate-Emitter threshold voltage		V _{GE (th)}	V _{CE} = 20V, I _C = 25mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	V _{CE (sat)} (terminal)	\/ - 15\/	T _j =25°C	-	2.25	2.70	- V
			V _{GE} = 15V I _C = 25A	T _j =125°C	-	2.60	-	
C.				T _j =150°C	-	2.65	-	
(V _{CE (sat)} (chip)	V _{GE} = 15V I _C = 25A	T _j =25°C	-	1.85	2.30	
				T _j =125°C	-	2.20	-	
				T _j =150°C	-	2.25	-	
Int	ternal gate resistance	Rg(int)	-		-	0	-	Ω
In	put capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	2.1	-	nF
	nput capacitance	ton			-	0.39	1.20	μs
Tu		t	Vcc = 600V		-	0.09	0.60	
		t r (i)	Ic = 25A -V _{GE} = +15 / -15V		-	0.03	-	
т.,	urn-off time	toff	$R_G = 39\Omega$		-	0.53	1.00	
lu	im-on time	t _r			-	0.06	0.30	
	Forward on voltage	V _F (terminal)	I _F = 25A	T _j =25°C	-	2.10	2.55	V
				T _j =125°C	-	2.25	-	
ļ				T _j =150°C	-	2.20	-	
FC		V _F (chip)	I _F = 25A	T _j =25°C	-	1.70	2.15	
				T _j =125°C	-	1.85	-	
				T _j =150°C	-	1.80	-	
Re	everse recovery time	t rr	I _F = 25A		-	-	0.35	μs
Ze	ero gate voltage collector current	Ices	V _{GE} = 0V V _{CE} = 1200V		-	-	1.0	m/
Gá	ate-Emitter leakage current	Iges	V _{CE} = 0V V _{GE} = +20 / -20V		-	-	200	nA
	Collector-Emitter saturation voltage	V _{CE (sat)} (terminal)	V _{GE} = 15V I _C = 25A	T _i =25°C	-	2.25	2.70	V
				T _i =125°C	-	2.60	-	
				T _i =150°C	-	2.65	-	
Co		V _{CE (sat)} (chip)	V _{GE} = 15V I _C = 25A	T _i =25°C	-	1.85	2.30	
Co				T _i =125°C	-	2.20	-	
				T _j =150°C	-	2.25	-	
Int	ternal gate resistance	Rg(int)	-	ļ.	-	0	-	Ω
		ton	V _{CE} = 600V		-	0.39	1.20	
Tu	Turn-on time	t _r	Ic = 25A		-	0.09	0.60	1
_		toff	V _{GE} = +15 / -15V		-	0.53	1.00	μs
Iu	ırn-off time	t _r	$R_{\rm G}$ = 39 Ω		-	0.06	0.30	1
Re	everse current	IRRM	V _R = 1200V		-	-	1.00	m/
	Forward on voltage	V _{FM} (chip)	I _F = 25A	terminal	-	1.80	2.25	
Fc				chip	-	1.42	-	\ \ \ \
Re	everse current	IRRM	V _R = 1600V	· ·	-	-	1.0	m
			T = 25°C		-	5000	-	
Resistance B value		R	T = 100°C		465	495	520	Ω
В	value	В	T = 25 / 50°C			3375	3450	К

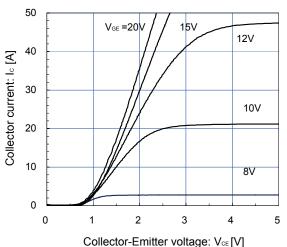
● Thermal resistance characteristics

Items	Symbols	Conditions	Cha	Characteristics		
items		Conditions	min.	typ.	max.	Units
	R _{th(j-e)}	Inverter IGBT	-	-	0.89	°C/W
Thermal registeres (Adevice)		Inverter FWD	-	-	1.06	
Thermal resistance (1device)		Brake IGBT	-	-	0.89	
		Converter Diode	-	-	0.97	
Contact thermal resistance (1device) (*4)	ntact thermal resistance (1device) (*4) R _{th(c-f)}		-	0.05	-	

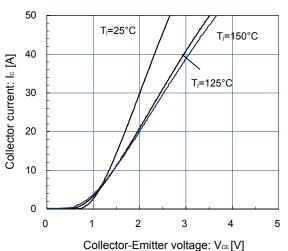
Note *4 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

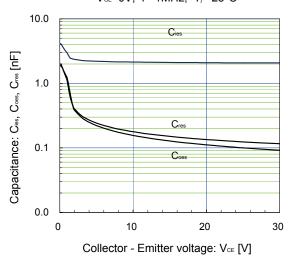
[Inverter] Collector current vs. Collector-Emitter voltage (typ.) T_j = 25°C / chip



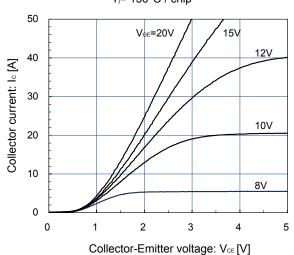
 $[\ Inverter\]$ Collector current vs. Collector-Emitter voltage (typ.) $V_{\text{GE}}\text{=}15V\ /\ chip}$



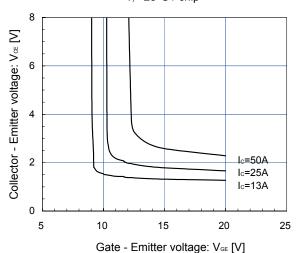
[Inverter] Capacitance vs. Collector-Emitter voltage (typ.) V_{GE} =0V, f= 1MHz, T_{j} = 25°C



 $[Inverter\]$ Collector current vs. Collector-Emitter voltage (typ.) $T_{j}{=}\ 150^{\circ}C\ /\ chip$



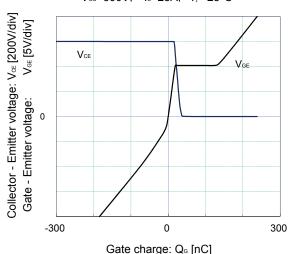
 $\label{eq:continuous} \begin{tabular}{ll} \b$

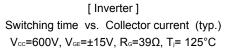


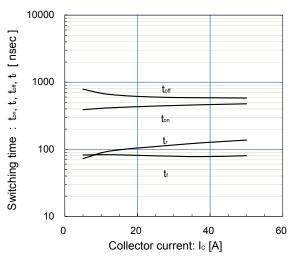
[Inverter]

Dynamic gate charge (typ.)

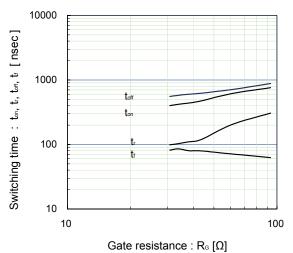
Vcc=600V, Ic=25A, T_i= 25°C



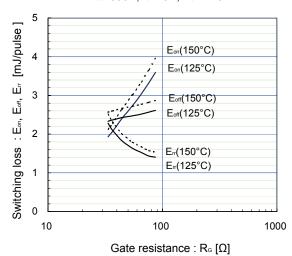




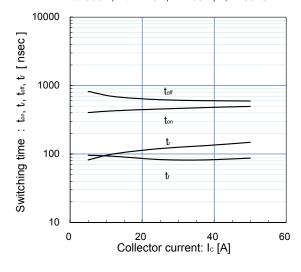
[Inverter] Switching time vs. gate resistance (typ.) $V_{co}=600V$, $I_{c}=25A$, $V_{GE}=\pm15V$, $T_{j}=125^{\circ}C$



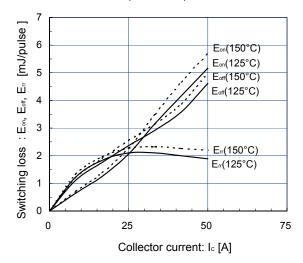
[Inverter] Switching loss vs. gate resistance (typ.) V_{cc} =600V, I_{c} =25A, V_{cE} =±15V



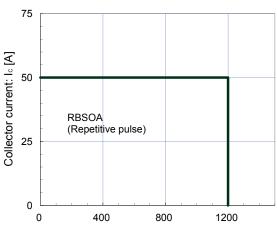
 $[\ Inverter\]$ Switching time vs. Collector current (typ.) $V_{\text{CC}}{=}600V,\ V_{\text{GE}}{=}\pm15V,\ R_{\text{G}}{=}39\Omega,\ T_{\text{J}}{=}\ 150^{\circ}C$



 $\label{eq:continuous} \begin{tabular}{ll} [Inverter] \\ Switching loss vs. Collector current (typ.) \\ V_{\text{CC}} = 600V, V_{\text{CE}} = \pm 15V, R_{\text{C}} = 39\Omega \\ \end{tabular}$



[Inverter] Reverse bias safe operating area (max.) $+V_{\text{GE}}=15V$, $-V_{\text{GE}}<=15V$, $R_{\text{G}}>=39\Omega$, $T_{\text{J}}=150^{\circ}\text{C}$

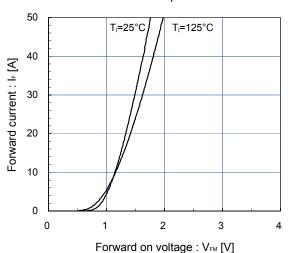


Collector-Emitter voltage : V_{CE} [V] (Main terminals)

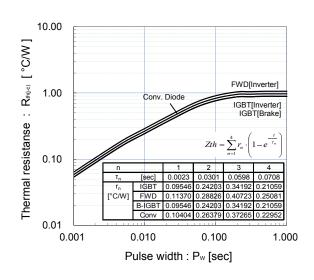
[Inverter] Forward current vs. forward on voltage (typ.) chip 50 T_j=25°C 40 Forward current : IF [A] 30 T_j=150°C 20 j=125°C 10 0 2 5 0 1 3

[Converter]
Forward current vs. forward on voltage (typ.)
chip

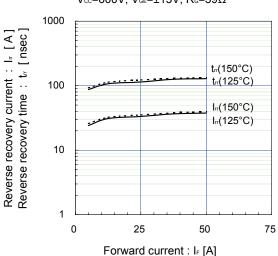
Forward on voltage : $V_F[V]$



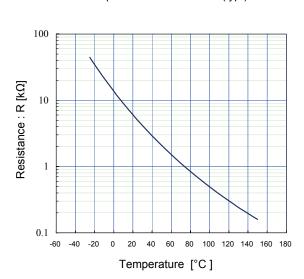
Transient thermal resistance (max.)



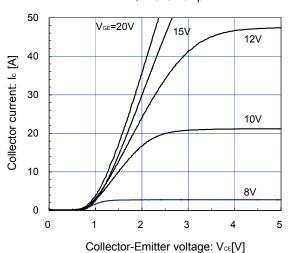
 $\label{eq:continuity} \begin{tabular}{ll} [Inverter] \\ Reverse recovery characteristics (typ.) \\ V_{cc} = 600V, \ V_{cc} = \pm 15V, \ R_c = 39\Omega \end{tabular}$



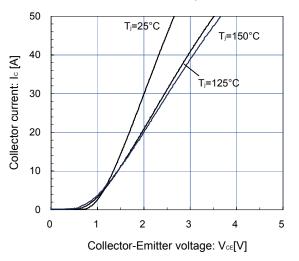
[Thermistor]
Temperature characteristic (typ.)



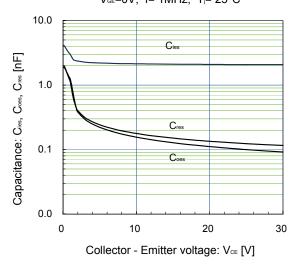
 $[\ Brake \]$ Collector current vs. Collector-Emitter voltage (typ.) $T_{j}{=}\ 25^{\circ}C\ /\ chip$



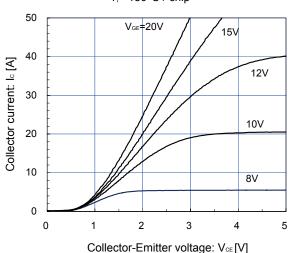
 $[\ Brake\]$ Collector current vs. Collector-Emitter voltage (typ.) $V_{\text{GE}}{=}15V\ /\ chip$



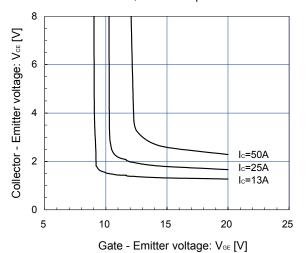
 $[\mbox{ Brake }] $$ Capacitance vs. Collector-Emitter voltage (typ.) $$ V_{\mbox{\tiny CE}}=0V, \mbox{ } f=1MHz, \mbox{ } T_{\mbox{\tiny J}}=25^{\circ}C $$$



[Brake] Collector current vs. Collector-Emitter voltage (typ.) $T_{j}{=}\ 150^{\circ}\text{C}\ /\ \text{chip}$



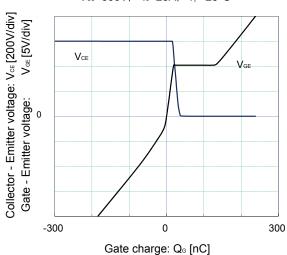
 $[\ \, Brake \]$ Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) $T_{j}{=}\ 25^{\circ}C\ /\ chip$



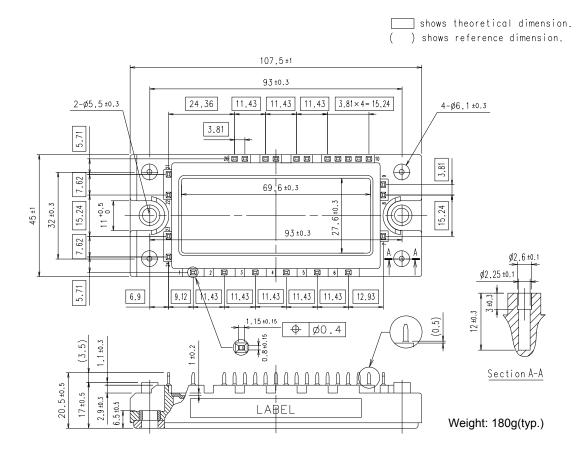
[Brake]

Dynamic gate charge (typ.)

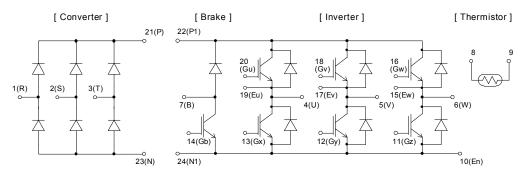
Vcc=600V, Ic=25A, T_j= 25°C



■ Outline Drawings (Unit: mm)



■ Equivalent Circuit



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WARNING

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- Communications equipment (terminal devices)
- Measurement equipment

- Machine tools
- Audiovisual equipment
- Electrical home appliances Person
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 - Emergency equipment for responding to disasters and anti-burglary devices
 - Medical equipment

- Trunk communications equipment
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- Safety devices
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